

Wireless Components

3-Band TV Tuner IC TUA6030, TUA6032 Version 2.1

Specification July 2001

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4-2	4-2	Div. components changed.		
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5-2	5-2	Junction temperature and storage temperature +125 °C max.		
5-5	5-5	Bus inputs SCL, SDA: V _{IH} = 2.3 V.		
5-8,5-9, 5-10	5-8,5-9, 5-10	Input conductance, input capacitance corrected.		
5-10	5-10	Phase noise @ ± 1 kHz frequency offset deleted. Phase noise, LOW band oscillator: $\Phi_{\rm OSC}$ = 92 dBc/Hz min @ ± 10 kHz. Phase noise, MID band oscillator: $\Phi_{\rm OSC}$ = 92 dBc/Hz min @ ± 10 kHz.		
5-11	5-11	Phase noise @ ± 1 kHz frequency offset deleted. Phase noise, HIGH band oscillator: $\Phi_{\rm OSC}$ = 87 dBc/Hz min.		
5-14	5-14	Table 5-5, Description of Symbols: CP and OS 'default' added		
5-15	5-15	Table 5-5, Test Modes: Normal operation 'default' added.		
5-14	5-14	Table 5-5, Description of Symbols: CP and OS 'default' added.		
5-15	5-15	Table 5-5, Test Modes: Normal operation 'default' added.		
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5-2	5-2	New definition of thermal properties.		
5-6	5-6, 5-7	Saturation Voltages for P0, 2, 3 added		
5-11 AGC take-over point: Min/max values added. Mixer output impedance: Values added				

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5-11, 5-12	5-11, 5-12					
5-16	5-16	Table 5-1, Defaults at power-on reset, Auxiliary byte, bit5 = 1.				
5-18	5-18 More telegram examples					
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Product Info

Product Info

General Description

The TUA6030, TUA6032 devices com- Package bine a mixer-oscillator block with a digitally programmable phase locked loop (PLL) for use in TV and VCR tuners.

Features

General

- Suitable for PAL/NTSC and Digital Video Broadcasting
- Wideband AGC detector for internal tuner AGC
 - 5 programmable take-over points
 - 2 programmable time constants
- Full ESD protection

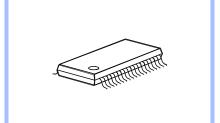
Mixer/Oscillator

- High impedance mixer input (common emitter) for LOW band
- Low impedance mixer input (common base) for MID band
- Low impedance mixer input (common base) for HIGH band
- 2 pin oscillator for LOW band
- 2 pin oscillator for MID band
- 4 pin oscillator for HIGH band

IF-Amplifier

IF preamplifier with symmetrical 75 Ω output impedance able to drive a SAW filter (500 Ω //40 pF)

The IC is suitable for PAL and NTSC tuners in TV- and VCR-sets or set-top receivers for analog TV and Digital Video Broadcasting.



- 4 independent I²C addresses
- I²C bus protocol compatible with 3.3 V and 5V micro-controllers up to 400 kHz
- Short lock-in time
- High voltage VCO tuning output
- 4 PNP ports
- 3 NPN ports
- 1 NPN port/ADC input
- Internal LOW/MID/HIGH band switch
- Lock-in flag
- Programmable reference divider ratio (24, 64, 80, 128)
- Programmable charge pump current
- The AGC stage makes the tuner AGC independent of the Video-IF AGC.

Ordering Information

Application

Туре	Ordering Code	Package
TUA6030	Q67037-A1146 (tape and reel)	P-TSSOP-38
TUA6032	Q67037-Axxxx (tape and reel)	P-TSSOP-38

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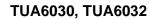




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Product Description

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Product Description

2.1 Overview

The **TUA6030**, **TUA6032** devices combine a mixer-oscillator block with a digitally programmable phase locked loop (PLL) for use in TV and VCR tuners.

The mixer-oscillator block includes three balanced mixers (one mixer with an unbalanced high-impedance input and two mixers with a balanced low-impedance input), two 2-pin asymmetrical oscillators for the LOW and the MID band, one 4-pin symmetrical oscillator for the HIGH band, an IF amplifier, a reference voltage, and a band switch.

The PLL block with four independently selectable chip addresses forms a digitally programmable phase locked loop. With a 4 MHz quartz crystal, the PLL permits precise setting of the frequency of the tuner oscillator up to 1024 MHz in increments of 31.25, 50, 62.5 or 166.7 kHz. The tuning process is controlled by a microprocessor via an I²C bus. The device has 8 output ports, one of them (P6) can also be used as ADC input port. A flag is set when the loop is locked. The lock flag can be read by the processor via the I²C bus.

2.2 Features

General

- Suitable for PAL/NTSC and Digital Video Broadcasting
- Wideband AGC detector for internal tuner AGC
 - 5 programmable take-over points
 - 2 programmable time constants
- Full ESD protection

Mixer/Oscillator

- High impedance mixer input (common emitter) for LOW band
- Low impedance mixer input (common base) for MID band
- Low impedance mixer input (common base) for HIGH band
- 2 pin oscillator for LOW band
- 2 pin oscillator for MID band
- 4 pin oscillator for HIGH band

IF-Amplifier

IF preamplifier with symmetrical 75 Ω output impedance able to drive a SAW filter (500 Ω //40 pF)

PLL

- 4 independent I²C addresses
- I²C bus protocol compatible with 3.3 V and 5V micro-controllers up to 400 kHz



Product Description

- Short lock-in time
- High voltage VCO tuning output
- 4 PNP ports
- 3 NPN ports
- 1 NPN port/ADC input
- Internal LOW/MID/HIGH band switch
- Lock-in flag
- Programmable reference divider ratio (24, 64, 80, 128)
- Programmable charge pump current

2.3 Application

- The IC is suitable for PAL and NTSC tuners in TV- and VCR-sets or cable set-top receivers for analog TV and **D**igital **V**ideo **B**roadcasting.
- The AGC stage makes the tuner AGC independent of the Video-IF AGC.

Recommended band limits in MHz:

Table 2-1 NTSC tuners					
	RF i	nput	Osci	llator	
Band	min	max	min	max	
LOW	55.25	127.25	101	173	
MID	133.25	361.25	179	407	
HIGH	367.25	801.25	413	847	

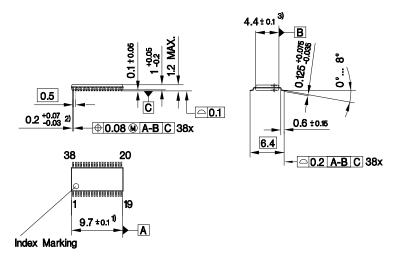
Table 2-2 PAL tuners					
RF input Oscillator					
Band	min	max	min	max	
LOW	44.25	154.25	83.15	193.15	
MID	161.25	439.25	200.15	478.15	
HIGH	447.25	863.25	486.15	902.15	

Note: Tuning margin of ±3 MHz not included.



2.4 Package Outlines

P-TSSOP-38

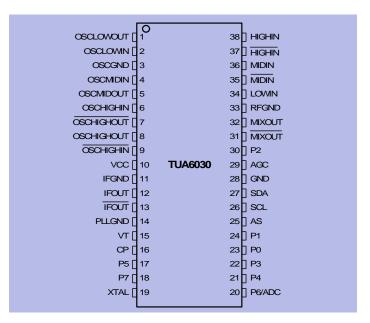


- 1) Does not include plastic or metal protrusion of 0.15 max. per side
- 2) Does not include dambar protrusion of 0.08 max. per side
- 3) Does not include plastic or metal protrusion of 0.25 max. per side $\frac{1}{2}$

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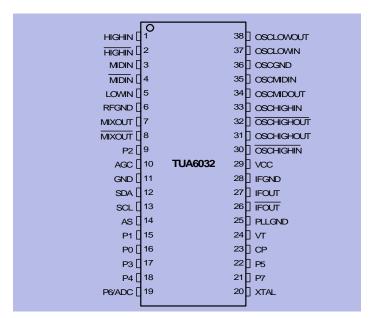


3.1 Pin Configuration



TUA6030 Pin_config

Figure 3-1 Pin Configuration TUA6030



TUA6032 Pin_config

Figure 3-2 Pin Configuration TUA6032



3.2 Pin Definition and Function

Remark: First pin number refers to TUA6030, second to TUA6032

Table 3-1 Pin Definition and Function							
Pin No.	Symbol	Equivalent I/O-Schematic	Aver	Average DC voltage			
140.			LOW	MID	HIGH		
1/38	OSCLOWOUT	1/38	2.2 V				
2/37	OSCLOWIN	2/37	1.5 V				
3/36	OSCGND	oscillator ground	0.0 V	0.0 V	0.0 V		
4/35	OSCMIDIN	5/34		1.5 V			
5/34	OSCMIDOUT	4/35		2.2 V			



Table 3-1 Pin Definition and Function (continued)						
Pin No.	Symbol	Equivalent I/O-Schematic	Aver	age DC vo	Itage	
			LOW	MID	HIGH	
6/33	OSCHIGHIN				4.037	
		ДД			1.8 V	
7/32	OSCHIGOUT	7/32			2.2 V	
0/04	00011100117	7/32 — 351				
8/31	OSCHIGOUT	6/33			2.2 V	
9/30	OSCHIGHIN	<u> </u>				
		Û			1.8 V	
						
10/29	VCC	supply voltage	5.0 V	5.0 V	5.0 V	
11/28	IFGND	IF ground	0.0 V	0.0 V	0.0 V	
12/27	IFOUT		2.1 V	2.1 V	2.1 V	
13/26	IFOUT	12/27	2.1 V	2.1 V	2.1 V	
14/25	PLLGND	PLL ground	0.0 V	0.0 V	0.0 V	
15/24	VT					
			VT	VT	VT	
16/23	СР	16/23	1.9 V	1.9 V	1.9 V	



Table 3-1 Pin Definition and Function (continued)							
Pin No.	Symbol	Equivalent I/O-Schematic	Average DC voltage				
			LOW	MID	HIGH		
17/22	P5	17/22 or 18/21	5 V or V _{CE}	5 V or V _{CE}	5 V or V _{CE}		
18/21	P7		5 V or V _{CE}	5 V or V _{CE}	5 V or V _{CE}		
19/20	XTAL	19/20	3.3 V	3.3 V	3.3 V		
20/19	P6/ADC	20/19	5 V or V _{CE}	5 V or V _{CE}	5 V or V _{CE}		
21/18	P4	21/18	5 V or V _{CE}	5 V or V _{CE}	5 V or V _{CE}		
22/17	P3		n.a.	n.a.	0 V or V _{CC} - V _{CE}		
23/16	P0	22/17 or	V _{CC} - V _{CE}	n.a.	n.a.		
24/15	P1	23/16 or	n.a.	V _{CC} - V _{CE}	n.a.		



Table 3-1 Pin Definition and Function (continued)								
Pin	Symbol	Equivalent I/O-Schematic	Aver	Average DC voltage				
No.								
			LOW	MID	HIGH			
25/14	AS		V_{AS}	V_{AS}	V_{AS}			
		Д						
		Ų						
		05/44						
		25/14						
		+,						
		'1 4						
		¥						
		ή						
		<u> </u>						
26/13	SCL		n.a.	n.a	n.a			
		Д						
		Ų						
		26/13						
		20/13						
		_ _						
27/12	SDA		n.a	n.a	n.a			
		ф						
		- \						
		27/12						
		l						
		<u></u>						
28/11	GND	ground	0.0	0.0	0.0			

Table 3	3-1 Pin Definition	and Function (continued)					
Pin	Symbol	Equivalent I/O-Schematic	-Schematic Average DC voltage				
No.							
			LOW	MID	HIGH		
29/10	AGC		3.0 V	3.0 V	3.0 V		
		Ų					
		لم					
		29/10					
		\perp					
30/9	P2		n.a.	n.a.	0 V or V _{CC} -		
		-			V _{CE}		
		\					
		30/9					
		_					
31/8	MIXOUT		4.0 V	4.0 V	4.0 V		
		Д					
		ŲŲ					
32/7	MIXOUT	31/8 32/7	4.0 V	4.0 V	4.0 V		
				-			
		Oscillator					
33/6	RFGND	IF ground	0.0 V	0.0 V	0.0 V		
34/5	LOWIN		1.9 V				
		34/5					
		¹ -					
		ή ή					
		<u> </u>					



Table 3	3-1 Pin Definition	and Function (continued)			
Pin No.	Symbol	Equivalent I/O-Schematic	Aver	ltage	
			LOW	MID	HIGH
35/4	MIDIN			0.75 V	
36/3	MIDIN	35/4		0.75 V	
37/2	HIGHIN				0.75 V
38/1	HIGHIN	37/2 38/1			0.75 V



3.3 Block Diagram

Remark: First pin number refers to TUA6030, second to TUA6032

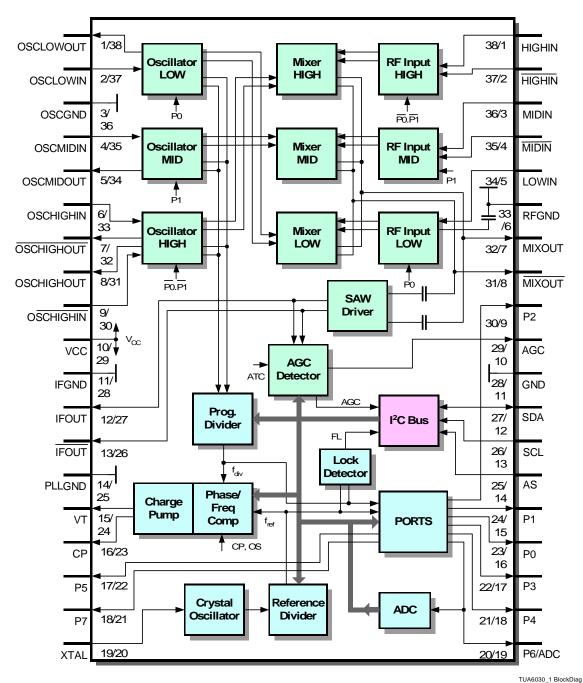


Figure 3-3 Block Diagram

3.4 Circuit Description

3.4.1 Mixer-Oscillator block

The mixer-oscillator block includes three balanced mixers (one mixer with an unbalanced high-impedance input and two mixers with a balanced low-impedance input), two 2-pin asymmetrical oscillators for the LOW and the MID band, one 4-pin symmetrical oscillator for the HIGH band, an IF amplifier, a reference voltage, and a band switch.

Filters between tuner input and IC separate the TV frequency signals into three bands. The band switching in the tuner front-end is done by using three PNP port outputs. In the selected band the signal passes a tuner input stage with a MOSFET amplifier, a double-tuned bandpass filter and is then fed to the mixer input of the IC which has in case of LOW band a high-impedance input and in case of MID or HIGH band a low-impedance input. The input signal is mixed there with the signal from the activated on chip oscillator to the IF frequency which is filtered out at the balanced mixer output pair by means of a parallel tuned circuit. The following IF amplifier is capacitively coupled to the mixer outputs and has a low output impedance to drive the SAW filter directly.

3.4.2 PLL block

The oscillator signal is internally DC-coupled as a differential signal to the programmable divider inputs. The signal subsequently passes through a programmable divider with ratio N = 256 through 32767 and is then compared in a digital frequency/phase detector with a reference frequency f_{ref} = 31.25, 50, 62.5 or 166.7 kHz. This frequency is derived from an unbalanced, low-impedance 4 MHz crystal oscillator (pin XTAL) divided by 128, 80,64 or 24. The reference frequencies will be different with a quartz other than 4 MHz.

The phase detector has two outputs which drive two current sources of a charge pump. If the negative edge of the divided VCO signal appears prior to the negative edge of the reference signal, the positive current source pulses for the duration of the phase difference. In the reverse case the negative current source pulses. If the two signals are in phase, the charge pump output (CP) goes into the high-impedance state (PLL is locked). An active low-pass filter integrates the current pulses to generate the tuning voltage for the VCO (internal amplifier, external pull-up resistor at VT and external RC circuitry). The charge pump output is also switched into the high-impedance state if the control bits T2, T1,T0 = 0, 1, 0. Here it should be noted, however, that the tuning voltage can alter over a long period in the high impedance state as a result of self discharge in the peripheral circuity. VT may be switched off by the control bit OS to allow external adjustments.

If the VCO is not oscillating the PLL locks to a tuning voltage of 33V (V_{TH}).



By means of control bit CP the pump current can be switched between two values by software. This programmability permits alteration of the control response of the PLL in the locked-in state. In this way different VCO gains can be compensated, for example.

The software controlled ports P0 to P7 are general purpose open-collector outputs. The test bits T2, T1, T0 =1, 0, 0 switch the test signals f_{div} (divided input signal) and f_{ref} (i.e.4 MHz / 64) to P4 and P5 respectively.

The lock detector resets the lock flag FL if the width of the charge pump current pulses is greater than the period of the crystal oscillator (i.e. 250 ns). Hence, if FL = 1, the maximum deviation of the input frequency from the programmed frequency is given by

$$\Delta f = \pm I_P * (K_{VCO} / f_{XTAL}) * (C1+C2) / (C1*C2)$$

where I_P is the charge pump current, K_{VCO} the VCO gain, f_{Xtal} the crystal oscillator frequency and C_1 , C_2 the capacitances in the loop filter (Chapter 4). As the charge pump pulses at i.e. 62.5 kHz (= f_{ref}), it takes a maximum of 16 μ s for FL to be reset after the loop has lost lock state.

Once FL has been reset, it is set only if the charge pump pulse width is less than 250 ns for eight consecutive f_{ref} periods. Therefore it takes between 128 and 144 μs for FL to be set after the loop regains lock.

3.4.3 AGC

The wide-band AGC stage detects the level of the IF output signal and generates an AGC voltage for gain control of the tuner input transistors. The AGC take-over and the time constant are selectable by the I²C bus.

3.4.4 I²C-Bus Interface

Data is exchanged between the processor and the PLL via the I²C bus. The clock is generated by the processor (input SCL). Pin SDA functions as an input or output depending on the direction of the data (open collector, external pull-up resistor). Both inputs have a hysteresis and a low-pass characteristic, which enhance the noise immunity of the I²C bus.

The data from the processor pass through an I²C bus controller. Depending on their function the data are subsequently stored in registers. If the bus is free, both lines will be in the marking state (SDA, SCL are high). Each telegram begins with the start condition and ends with the stop condition. Start condition: SDA goes low, while SCL remains high. Stop condition: SDA goes high while



SCL remains high. All further information transfer takes place during SCL = low, and the data is forwarded to the control logic on the positive clock edge.

The table 'Bit Allocation' (see Table 5-4 Bit Allocation Read / Write on page 39) should be referred to for the following description. All telegrams are transmitted byte-by-byte, followed by a ninth clock pulse, during which the control logic returns the SDA line to low (acknowledge condition). The first byte is comprised of seven address bits. These are used by the processor to select the PLL from several peripheral components (address select). The LSB bit (R/W) determines whether data are written into (R/W = 0) or read from (R/W = 1) the PLL.

In the data portion of the telegram during a WRITE operation, the MSB bit of the first or third data byte determines whether a divider ratio or control information is to follow. In each case the second byte of the same data type has to follow the first byte. Appropriate setting of the test bits will decide whether the band-switch byte or the auxiliary byte will be transmitted (see Table 5-7 Test modes on page 40).

If the address byte indicates a READ operation, the PLL generates an acknowledge and then shifts out the status byte onto the SDA line. If the processor generates an acknowledge, a further status byte is output; otherwise the data line is released to allow the processor to generate a stop condition. The status word consists of three bits from the A/D converter, the lock flag and the power-on flag.

Four different chip addresses can be set by an appropriate DC level at pin AS (see Table 5-6 Address selection on page 40).

While the supply voltage is applied, a power-on reset circuit prevents the PLL from setting the SDA line to low, which would block the bus. The power-on reset flag POR is set at power-on and if V_{CC} falls below 3.2 V. It will be reset at the end of a READ operation.

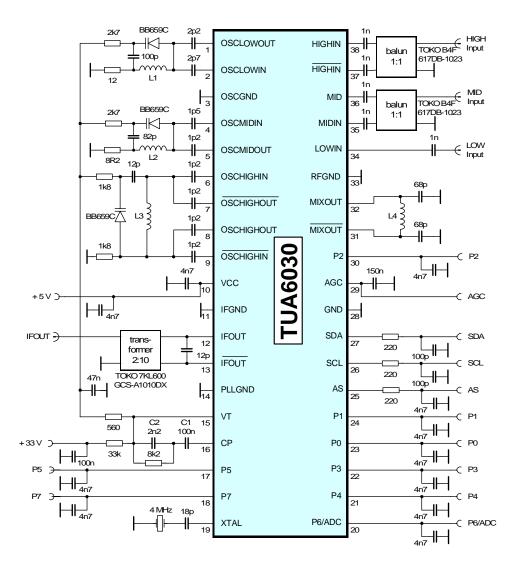
4 Applications

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4.1 Circuits

Remark: Pinning refers to TUA6030



App Circuit Ntsc

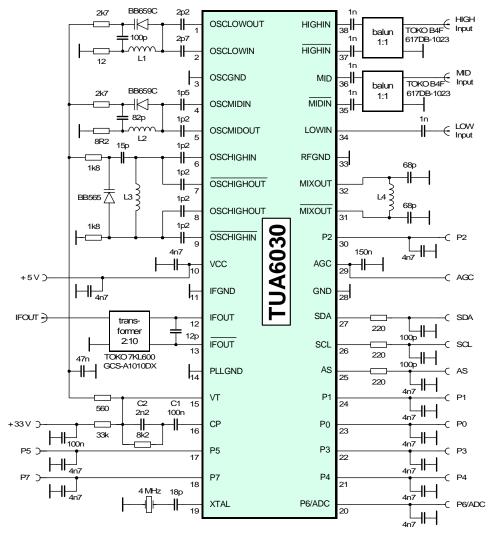
Figure 4-1 Application Circuit for NTSC

Recommended band limits in MHz							
	RF i	nput	Oscillator				
	min max		min	max			
LOW	55.25	127.25	101	173			
MID	133.25	361.25	179	407			
HIGH	367.25	801.25	413	847			

Coils							
	turns	Ø	wire Ø				
L1	8.5	3.2 mm	0.5 mm				
L2	3.5	2.5 mm	0.5 mm				
L3	1.5	2.4 mm	0.5 mm				
L4	12.5	3.5 mm	0.3 mm				



Remark: Pinning refers to TUA6030



App Circuit PAL

Figure 4-2 Application Circuit for PAL

Recommended band limits in MHz							
	RFi	nput	Oscillator				
	min max		min	max			
LOW	44.25	154.25	83.15	193.15			
MID	161.25	439.25	200.15	478.15			
HIGH	447.25	863.25	486.15	902.15			

Coils							
	turns	Ø	wire Ø				
L1	8.5	3.2 mm	0.5 mm				
L2	2.5	3 mm	0.5 mm				
L3	1.5	2.4 mm	0.5 mm				
L4	14.5	4 mm	0.3 mm				

Cont	ents of this Chapter
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5.1 Electrical Data

5.1.1 Absolute Maximum Ratings



WARNING

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC may result.

Parameter ^{1).}	Symbol	Limit	Limit Values		Remarks
		min	max		
Supply voltage	V _{CC}	-0.3	6	V	
Ambient temperature	T _A	-10	T _{Amax} 2).	°C	
Storage temperature	T _{Stg}	-40	+125	°C	
Junction temperature	T _J		+ 125	°C	
Temperature difference junction to case ^{3).}	T _{JC}		2	К	
PLL					
СР	V _{CP}	-0.3	3	V	
	I _{CP}		1	mA	
Crystal oscillator pin XTAL	V_{Q}		6	V	
	IQ	-5		mA	
Bus input/output SDA	V _{SDA}	-0.3	6	V	
Bus output current SDA	I _{SDA(L)}		10	mA	open collector
Bus input SCL	V _{SCL}	-0.3	6	V	
Chip address switch AS	V _{AS}	-0.3	6	V	
VCO tuning output (loop filter)	V _{VT}	-0.3	35	V	



Table 5-1 Absolute Maximum Ratings, ambient temperature T _{AMB} = - 10°C + 85°C (continued)							
Parameter ^{1.)}	Symbol	Limit	Values	Unit	Remarks		
		min	max				
NPN port output voltage	V _{P4, 5, 7}	-0.3	6	V	open collector		
NPN port output current	I _{P4, 5, 7(L)}	-1	10	mA	open collector, t _{max} = 0.1 sec. at 5.5 V		
P6/ADC input/output voltage	V _{P6/ADC}	-0.3	6	V			
NPN port output current	I _{P6/ADC(L)}	-1	10	mA	open collector, t _{max} = 0.1 sec. at 5.5 V		
PNP port output voltage	V _{P0, 1, 2, 3}	-0.3	6	V	open collector		
PNP port output current	I _{P1(L)}	+1	-25	mA	open collector, t _{max} = 0.1 sec. at 5.5 V		
PNP port output current	I _{PO(L)}	+1	-10	mA	open collector, t _{max} = 0.1 sec. at 5.5 V		
PNP port output current	I _{P2, 3(L)}	+1	-5	mA	open collector, t _{max} = 0.1 sec. at 5.5 V		
Total port output current of NPN ports	$\Sigma I_{P(L)}$		40	mA	t _{max} = 0.1 sec. at 5.5 V		
Total port output current of PNP ports	$\Sigma I_{P(L)}$		-40	mA	t _{max} = 0.1 sec. at 5.5 V		
Mixer-Oscillator							
Mix inputs LOW band	V_{LOW}	-0.3	3	V			
Mix inputs MID/HIGH band	V _{MID/HIGH}		2	V			
	I _{MID/HIGH}	-5	6	mA			
VCO base voltage	V _B	-0.3	3	V	LOW, MID and HIGH band oscillators		
VCO collector voltage	V _C		6	V	LOW, MID and HIGH band oscillators		
ESD-Protection ^{4).}							
all pins	V _{ESD}		2	kV			

^{1).} All values are referred to ground (pin), unless stated otherwise.

Currents with a positive sign flow into the pin and currents with a negative sign flow out of pin.

^{2).} The maximum ambient temperature depends on the mounting conditions of the package. Any application mounting must guarantee not to exceed the maximum junction temperature of 125 °C. As reference the temperature difference junction to case is given.

^{3).} Referred to top center of package.

^{4).} According to EIA/JESD22-A114-B (HBM in-circuit test), as a single device in-circuit contact discharge test.

5.1.2 Operating Range

Within the operational range the IC operates as described in the circuit description. The AC / DC characteristic limits are not guaranteed.

Table 5-2 Operating Range								
Parameter	Symbol	Limit Values L		Unit	Test Conditions	L	Item	
		min	max					
Supply voltage	V _{CC}	+4.5	+5.5	V				
Programmable divider factor	N	256	32767					
LOW mixer input frequency range	f _{MIXV}	30	200	MHz				
MID and HIGH band mixer input frequency range	f _{MIXU}	130	900	MHz				
LOW oscillator frequency range	f _{OH}	65	250	MHz				
MID band oscillator frequency range	f _{OU}	165	530	MHz				
HIGH band oscillator frequency range	f _{OU}	400	950	MHz				
Ambient temperature	T _{AMB}	-10	T _{Amax} 1).	°C				

^{1).} see 5.1.1 Absolute Maximum Ratings on page 27



5.1.3 AC/DC Characteristics

Table 5-3 AC/DC Charac		1 T _{AMB} = 2	25 °C, V _{CC}	= 5V				
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
Supply								
Supply voltage	V _{CC}	4.5	5	5.5	V			
Current consumption	I _{VCC}		73		mA	LOW band		
	I _{VCC}		75		mA	MID band		
	I _{VCC}	-	66		mA	HIGH band		
Digital Part								
PLL								
Crystal oscillator connec	tions XTAL							
Crystal frequency	f _{XTAL}	3.2	4.0	4.48	MHz	series resonance		
Crystal resistance	R _Q	25		300	Ω	series resonance		
Input impedance	Z _Q	-1000	-1200		Ω	f _{XTAL} = 4 MHz		
Charge pump output CP								
High-level output current	I _{CPH}		±280		μA	CP = 1, V _{CP} = 2 V		
Low-level output current	I _{CPL}		±60		μA	CP = 0, V _{CP} = 2 V		
Tristate current	I _{CPZ}		+1		nA	T2, T1, T0 = 0, 1, 0, V _{CP} = 2 V		
Output voltage	V _{CP}	1.0		2.5	V	loop closed		
Tuning voltage output VT	(open colle	ctor)						
Leakage current	I _{TH}			10	μΑ	V _{TH} = 33 V, OS = 1		
Output voltage when the loop is closed, (test mode in normal operation)	V _{TL}	0.4		32.7	V	OS=0, $R_{Load} = 33 \text{ k}\Omega$, tuning supply = 33 V		
I ² C-Bus								
Bus inputs SCL, SDA								
High-level input voltage	V _{IH}	2.3		5.5	V			
Low-level input voltage	V _{IL}	0		1.5	V			
High-level input current	I _{IH}			10	μA	$V_{bus} = 5.5 \text{ V},$ $V_{CC} = 0 \text{ V}$		
	I _{IH}			10	μA	$V_{bus} = 5.5 \text{ V},$ $V_{CC} = 5.5 \text{ V}$		



Table 5-3 AC/DC Charac								
	Symbol		imit Value	es	Unit	Test Conditions	L	Iten
		min	typ	max				
Low-level input current	I _{IL}			10	μA	$V_{bus} = 1.5 \text{ V},$ $V_{CC} = 0 \text{ V}$		
	I _{IL}	-10			μA	$V_{bus} = 0 V,$ $V_{CC} = 5.5 V$		
Bus output SDA (open co	ollector)							
Leakage current	I _{OH}			10	μA	V _{OH} = 5.5 V		
Low-level output voltage	V _{OL}			0.4	V	I _{OL} = 3 mA		
Low-level output voltage	V _{OL}			0.6	V	I _{OL} = 6 mA at 400 kHz		
Edge speed SCL,SDA								
Rise time	t _r			300	ns			
Fall time	t _f			300	ns			
Clock timing SCL								
Frequency	f _{SCL}	0	100	400	kHz			
High pulse width	t _H	0.6			μs			
Low pulse width	t_	1.3			μs			
Start condition								
Set-up time	t _{susta}	0.6			μs			
Hold time	t _{hsta}	0.6			μs			
Stop condition								
Set up time	t _{susto}	0.6			μs			
Bus free	t _{buf}	1.3			μs			
Data transfer								
Set-up time	t _{sudat}	0.1			μs			
Hold time	t _{hdat}	0			μs			
Input hysteresis SCL, SDA	V _{hys}		200		mV			
Pulse width of spikes which are suppressed	t _{sp}	0		50	ns			
Capacitive load for each bus line	C _L			400	pF			
PNP port outputs P0, P1,	P2, P3 (oper	n collecto	r)	-	•			
Output leakage current	I _{POH0to3}			-10	μΑ	V _{CC} = 5.5 V		
Output saturation voltage port 0	V _{PL0}		0.25	0.4	V	I _{POL0} = 10 mA		
Output saturation voltage port 1	V _{PL1}		0.25	0.4	V	I _{POL1} = 15 mA		



Table 5-3 AC/DC Charac	teristics with	1 T _{AMB} = 2	25 °C, V _{CC}	= 5V (con	tinued)			
	Symbol		imit Value		Unit	Test Conditions	L	Item
		min	typ	max				
Output saturation voltage ports 2, 3	V _{PL2,3}		0.25	0.4	V	I _{POL2, 3} = 5 mA		
NPN port outputs P4, P5,	P6, P7 (ope	n collecto	r)					
Output leakage current	I _{POH4to7}			10	μA	V _{CC} = 5.5, V _{Pn4to7} = 6 V		
Output saturation voltage	V _{PL04to7}		0.25	0.4	V	I _{POL4to7} = 5 mA		
ADC input								
ADC input voltage	V _{ADC}	0		5.5	V			
High-level input current	I _{ADCH}			10	μA			
Low-level input current	I _{ADCL}	-10			μA			
Address selection input	AS							
High-level input current	I _{ASH}			50	μA	V _{ASH} = 5.5 V		
Low-level input current	I _{ASL}	-50			μA	V _{ASL} = 0 V		
Analog Port								
Analog Part LOW band mixer mode (F	00 - 1 D1 -0	including	ı IE ampli	fior)				
RF frequency	f _{RF}	44.25	jii ailipii	170.25	MHz	picture carrier ^{1).}		
Voltage gain	G _V	23.5	26	28.5	dB	f _{RF} = 44.25 MHz,		
						see 5.5.1 on page 46		
	G _V	23.5	26	28.5	dB	f _{RF} = 170.25 MHz, see 5.5.1 on page 46		
Noise figure	NF		8	10	dB	f _{RF} = 50 MHz, see 5.5.4 on page 47,		
						see 5.5.3 on page 47		
Output voltage causing 0.3% of crossmodulation	Vo	108	111		dΒμV	f _{RF} = 44.25 MHz, see 5.5.6 on page 48		
in channel	V _O	108	111		dΒμV	f _{RF} = 170.25 MHz, see 5.5.6 on page 48		
Output voltage causing	V _O	108	111		dΒμV	f _{RF} = 44.25 MHz ^{2).}		
1.1 kHz incidental FM	Vo	108	111		dΒμV	f _{RF} = 170.25 MHz ^{2.)}		
Local oscillator FM caused by I ² C communication	FM _{I2C}			2.12	kHz	f _{RF} = 170.25 MHz ^{3).}		
750 Hz Pulling	V _i	88			dΒμV	f _{RF} = 154.25 MHz ^{4).}		
Channel S02 beat	INT _{S02}	57	60		dBc	V _{RFpix} = 115 dBμV at IF output ^{5).}		



Table 5-3 AC/DC Charac	teristics with	1 T _{AMB} = 2	5 °C, V _{CC}	= 5V (con	tinued)			
	Symbol	L	imit Value	es	Unit	Test Conditions	L	ltem
		min	typ	max				
Channel A-5 beat	INT _{A-5}	57	60		dBc	$V_{RFpix} = 115 \text{ dB}\mu\text{V}$ at IF output ^{6).}		
Channel CH6 color beat	INT _{CH6}	63	66		dBc	$V_{RFpix} = 80 \text{ dB}\mu V$ $V_{RFsnd} = 80 \text{ dB}\mu V^{7)}$.		
RF input level without lock-out	V _i			120	dΒμV	8).		
Input conductance	9 _i		1		mS	f _{RF} = 44.25 MHz, see 5.4.1 on page 43		
	9i		1		mS	f _{RF} = 170.25 MHz, see 5.4.1 on page 43		
Input capacitance	C _{MixV}		1		pF	f _{RF} = 44.25 to 170.25 MHz, see 5.4.1 on page 43		
Mid band mixer mode (Po) = 0, P1 =1, i	including	IF amplifi	er)				
RF frequency	f _{RF}	154.25		454.25		picture carrier 1.)		
Voltage gain	G _V	33	36	39	dB	f _{RF} = 154.25 MHz, see 5.5.2 on page 46		
	G _V	33	36	39	dB	f _{RF} = 454.25 MHz, see 5.5.2 on page 46		
Noise figure (not corrected for image)	NF		6	8	dB	f _{RF} = 154.25 MHz, see 5.5.5 on page 48		
	NF		6	8	dB	f _{RF} = 300 MHz, see 5.5.5 on page 48		
Output voltage causing 0.3% of crossmodulation	V _O	108	111		dΒμV	f _{RF} = 154.25 MHz, see 5.5.7 on page 49		
in channel	V _O	108	111		dΒμV	f _{RF} = 454.25 MHz, see 5.5.7 on page 49		
Output voltage causing	V _O	108	111		dΒμV	f _{RF} = 154.25 MHz ^{2.)}		
1.1 kHz incidental FM	V _O	108	111		dΒμV	f _{RF} = 454.25 MHz ^{2.)}		
Local oscillator FM caused by I ² C communication	FM _{I2C}			2.12	kHz	f _{RF} = 454.25 MHz ^{3.)}		
N+5 - 1 MHz pulling	N+5 - 1 MHz	77	80		dΒμV	$f_{RFw} = 359.25 \text{ MHz},$ $f_{OSC} = 398.15 \text{ MHz},$ $f_{RFu} = 399.25 \text{ MHz}^{9)}.$		



Table 5-3 AC/DC Charac	teristics with	1 T _{AMB} = 2	5 °C, V _{CC}	= 5V (con	tinued)			
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
750 Hz Pulling	V _i	78			dΒμV	f _{RF} = 439.25 MHz ^{4.)}		
RF input level without lock-out	V _i			120	dΒμV	8.)		
Input impedance $Z_i = (R_s + j\omega L_s)$	R_s		35		Ω	f _{RF} = 154.25.25 MHz, see 5.4.2 on page 43		
	R _s		30		Ω	f _{RF} = 454.25 MHz, see 5.4.2 on page 43		
	L _s		5		nH	f _{RF} = 154.25.25 MHz, see 5.4.2 on page 43		
	L _s		4.5		nH	f _{RF} = 454.25 MHz, see 5.4.2 on page 43		
HIGH band mixer mode (F	P0 = 0, P1 = 0	0, includin	g IF ampl	ifier)				
RF frequency	f _{RF}	399.25		863.25		picture carrier 1.)		
Voltage gain	G _V	33	36	39	dB	f _{RF} = 407.25 MHz, see 5.5.2 on page 46		
	G _V	33	36	39	dB	f _{RF} = 863.25 MHz, see 5.5.2 on page 46		
Noise figure (not corrected for image)	NF		6	8	dB	f _{RF} = 407.25 MHz, see 5.5.5 on page 48		
	NF		7	9	dB	f _{RF} = 863.25 MHz, see 5.5.5 on page 48		
Output voltage causing 0.3% of crossmodulation	V _O	108	111		dΒμV	f _{RF} = 407.25 MHz, see 5.5.7 on page 49		
in channel	V _O	108	111		dΒμV	f _{RF} = 863.25 MHz, see 5.5.7 on page 49		
Output voltage causing	V _O	108	111		dΒμV	f _{RF} = 407.25 MHz ^{2.)}		
1.1 kHz incidental FM	V _O	108	111		dΒμV	f _{RF} = 454.25 MHz ^{2.)}		
Local oscillator FM caused by I ² C communication	FM _{I2C}			2.12	kHz	f _{RF} = 863.25 MHz ^{3.)}		
N+5 - 1 MHz pulling	N+5 - 1 MHz	77	80		dΒμV	$f_{RFw} = 823.25 \text{ MHz},$ $f_{OSC} = 862.15 \text{ MHz},$ $f_{RFu} = 862.25 \text{ MHz}^{9.)}$		
750 Hz Pulling	Vi	78			dΒμV	f _{RF} = 855.25 MHz ^{4.)}		



Table 5-3 AC/DC Charact						Test Conditions		14
	Symbol		imit Value		Unit	rest Conditions	L	lten
RF input level without	V _i	min	typ	max 120	dΒμV	8.)		
lock-out	V I			120	αБμν	0.)		
Input impedance	R_s		35		Ω	f _{RF} = 407.25 MHz,		
$Z_i = (R_s + j\omega L_s)$	_					see 5.4.3 on page 44		
	R _s		30		Ω	f _{RF} = 863.25 MHz, see 5.4.3 on page 44		
	L _s		5		nΗ	f _{RF} = 407.25 MHz,		
	1		4.5		nH	see 5.4.3 on page 44		
	L _s		4.5		Ш	f _{RF} = 863.25 MHz, see 5.4.3 on page 44		
LOW band oscillator, Cha	pter 4							
Oscillator frequency	fosc	80		210	MHz	10).		
Oscillator frequency shift	$\Delta f_{OSC(V)}$		20	70	kHz	$\Delta V_{CC} = 5 \% ^{11)}$.		
	Δf _{OSC(V)}		110		kHz	ΔV _{CC} = 10 % ^{11.)}		
Oscillator frequency drift	$\Delta f_{OSC(T)}$		300	500	kHz	$\Delta T = 25$ °C, with compensation 12).		
Oscillator frequency drift	$\Delta f_{OSC(t)}$		150	250	kHz	5 s to 15 min after switch on ^{13).}		
Phase noise, carrier to noise sideband	$\Phi_{\sf OSC}$	88	92		dBc/ Hz	±10 kHz frequency offset, worst case in frequency range		
Ripple susceptibility of V_P	RSC	15	20		mV	4.75 V < VP < 5.25 V, worst case in fre- quency range, ripple frequency 500 kHz 14).		
MID band oscillator, Chap	oter 4							
Oscillator frequency	f _{OSC}	201		493	MHz	10.)		
Oscillator frequency shift	$\Delta f_{OSC(V)}$		20	70	kHz	$\Delta V_{CC} = 5 \% ^{11.)}$		
	$\Delta f_{OSC(V)}$		110		kHz	$\Delta V_{CC} = 10 \% ^{11.)}$		
Oscillator frequency drift	$\Delta f_{OSC(T)}$		500	750	kHz	$\Delta T = 25$ °C; with compensation ^{12.)}		
Oscillator frequency drift	$\Delta f_{OSC(t)}$		250	500	kHz	5 s to 15 min after switch on ^{13.)}		
Phase noise, carrier to noise sideband	$\Phi_{\sf OSC}$	86	92		dBc/ Hz	±10 kHz frequency offset, worst case in frequency range		



Table 5-3 AC/DC Charact								
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Iten
		min	typ	max				
Ripple susceptibility of V _P	RSC	15	20		mV	4.75 < VP < 5.25 V, worst case in fre- quency range, ripple frequency 500 kHz 14.)		
HIGH band oscillator, Cha	pter 4							
Oscillator frequency	fosc	435		905	MHz	10.)		
Oscillator frequency shift	$\Delta f_{OSC(V)}$		20	70	kHz	$\Delta V_{CC} = 5 \% ^{11.)}$		
	$\Delta f_{OSC(V)}$		300		kHz	$\Delta V_{CC} = 10 \% ^{11.)}$		
Oscillator frequency drift	$\Delta f_{OSC(T)}$		600	1000	kHz	$\Delta T = 25$ °C; with compensation ^{12.)}		
Oscillator frequency drift	$\Delta f_{OSC(t)}$		250	500	kHz	5 s to 15 min after switch on ^{13).}		
Phase noise, carrier to noise sideband	$\Phi_{\sf OSC}$	86	90		dBc/ Hz	±10 kHz frequency offset, worst case in frequency range		
Ripple susceptibility of V _P	RSC	15	20		mV	4.75 < VP < 5.25 V, worst case in fre- quency range, ripple frequency 500 kHz 14.)		
IF amplifier								
Mixer output impedance $Y_0 = Gs + j\omega C_s$	Gp		3		mS	at 36 MHz, see 5.4.4 on page 44		
	Ср		4		pF	at 36 MHz, see 5.4.4 on page 44		
IF amplifier output impedance	R _S		65		Ω	at 36 MHz, see 5.4.5 on page 45		
$Z_0 = R_S + j\omega L_S$	L _S		20		nH	at 36 MHz, see 5.4.5 on page 45		
Rejection at the IF output	s							
Level of divider interferences in the IF signal	INT _{DIV}			20	dΒμV	^{15).} , worst case		
Crystal oscillator interferences rejection	INT _{XTAL}	60	66		dBc	$V_{IF} = 100 \text{ dB}\mu\text{V},$ worst case in frequency range ^{16).}		
Reference frequency rejection	INT _{REF}	60	66		dBc	V _{IF} = 100 dBμV, worst case in fre- quency range ^{17).}		
AGC output								
AGC take-over point	AGC _{TOP}	111	112	113	dΒμV	AL2, AL1, AL0 = 0, 1,0		

Table 5-3 AC/DC Characteristics with T _{AMB} = 25 °C, V _{CC} = 5V _C (continued)								
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
Source current 1	AGC _{fast}	7.2	9.0	10.8	μΑ			
Source current 2	AGC _{slow}	185	220	264	nA			
Peak sink to ground	AGC _{peak}	80	100	120	μA			
AGC output voltage	V _{AGCmax}	3.3	3.5	3.7	V	maximum level		
AGC output voltage	V _{AGCmin}	0		0.25	V	minimum level		
RF voltage range to switch the AGC from active to inactive mode	AGC _{SLIP}			0.5	dB			
AGC output voltage	AGC _{RML}	0		2.9	V	AGC bit high or AGC active		
AGC output voltage	AGC _{RMH}	3	3.5	VCC- 0.5 or 4	V	AGC bit low or AGC inactive		
AGC leakage current	AGC _{LEAK}	-50		50	nA	AL2, AL1, AL0 = 1,1,0 0 < V _{AGC} < V _{CC}		
AGC output voltage	AGC _{OFF}	3.3	3.5	VCC- 0.5 or 4	V	AL2, AL1, AL0 = 1,1,1 AGC is disabled		

- This value is only guaranteed in lab.
 - 1). The RF frequency range is defined by the oscillator frequency range and the intermediate frequency (IF).
 - 2). This is the level of the RF unwanted signal (50% amplitude modulated with 1kHz) that causes a 1.1 kHz FM modulation of the local oscillator and thus of the wanted signal; $V_{wanted} = 100 \text{ dB}\mu\text{V}$; $f_{unwanted} = f_{wanted} + 5.5 \text{ MHz}$.
 - 3). Local oscillator FM modulation resulting from I^2C communication is measured at the IF output using a modulation analyser with a peak to peak detector (($P_+ + P_-$)/2) and a post detection filter 30 Hz 200 kHz. The I^2C messages are sent to the tuner in such a way that the tuner is addressed but the content of the PLL registers are not altered. The refresh interval between each data set shall be 20 ms to 1s.
 - 4). This is the level of the RF signal (100% amplitude modulated with 11.89 kHz) that causes a 750 Hz frequency deviation on the oscillator signal producing sidebands 30 dB below the level of the oscillator signal.
 - 5). Channel S02 beat is the interfering product of f_{RFpix} , f_{IF} and f_{OSC} of channel S02, f_{BEAT} = 37.35 MHz. The possible mechanisms are f_{OSC} 2 x f_{IF} or 2 x f_{RFpix} f_{OSC} .
 - 6). Channel A-5 beat is the interfering product of \dot{f}_{RFpix} , f_{IF} and f_{OSC} of channel A-5; f_{BEAT} = 45.5 MHz. The possible mechanisms are: f_{OSC} 2 x f_{RFpix} f_{OSC} .
 - 7). Channel 6 beat is the interfering product of f_{RFpix} + f_{RFsnd} f_{OSC} of channel 6 at 42 MHz.
 - 8). The IF output signal stays stable within the range of the f_{ref} step for a low level RF input up to 120 dB μ V.
 - 9). N+5 -1 MHz is defined as the input level of channel N+5, at frequency 1 MHz lower, causing FM sidebands 30 dB below the wanted carrier.
 - 10). Limits are related to the tank circuit used in the application board (Chapter 4). Frequency bands may be adjusted by the choice of external components.
 - 11). The frequency shift is defined as a change in oscillator frequency when the supply voltage varies from V_{CC} = 5 to 4.75 V (4.5 V) or from V_{CC} = 5 to 5.25 V (5.5 V). The oscillator is free running during this measurement.
 - 12). The frequency drift is defined as a change in oscillator frequency if the ambient temperature varies from T_{amb} = 25 to 50 °C or from T_{amb} = 25 to 0 °C. The oscillator is free running during this measurement.



- 13). The switch-on drift is defined as a change in oscillator frequency between 5 s and 15 min after switch-on. The oscillator is free running during this measurement.
- 14). The supply ripple susceptibility is measured in the application board (Chapter 4), using a spectrum analyser connected to the IF output. An unmodulated RF signal is applied to the test board RF input. A sinewave signal with a frequency of 500 kHz is superposed onto the supply voltage (see 5.5.8 on page 49). The amplitude of this ripple is adjusted to bring the 500 kHz sidebands around the IF carrier to a level of 53.5 dBc referred to the carrier.
- 15). This is the level of divider interferences close to the IF frequency. For example channel S3: f_{OSC} = 158.15 MHz, 1/4 f_{OSC} = 39.5375 MHz. Divider interference is measured with the application board (Chapter 4). All ground pins are connected to a single ground plane under the IC. The LOWIN input must be left open (i.e. not connected to any load or cable). The MIDIN and HIGHIN inputs are connected to a hybrid. The measured level of divider interference are influenced by layout, grounding and port decoupling. The measurement results between various applications and the reference board could vary as much as 10 dB.
- 16). Crystal oscillator interference means the 4 MHz sidebands caused by the crystal oscillator. The rejection has to be greater than 60 dB for an IF output of 100 dB μ V.
- 17). The reference frequency rejection is the level of reference frequency sidebands (e.g. 62.5 kHz) related to the carrier. The rejection has to be greater than 60 dB for an IF output of 100 dBμV.



5.2 Programming

Table 5-4 Bit Allocation Read / Write										
Name	Byte		Bits						Ack	
		MSB	bit6	bit5	bit4	bit3	bit2	bit1	LSB	
Write Data										
Address Byte	ADB	1	1	0	0	0	MA1	MA0	R/ W=0	Α
Divider Byte 1	DB1	0	N14	N13	N12	N11	N10	N9	N8	Α
Divider Byte 2	DB2	N7	N6	N5	N4	N3	N2	N1	N0	Α
Control byte	СВ	1	СР	T2	T1	T0	RSA	RSB	os	Α
Bandswitch byte	BB	P7	P6	P5	P4	P3	P2	P1	P0	Α
Auxiliary byte 1).	AB	ATC	AL2	AL1	AL0	0	0	0	0	Α
Read data										
Address byte	ADB	1	1	0	0	0	MA1	MA0	R/ W=1	Α
Status byte	SB	POR	FL	1	1	AGC	A2	A1	A0	Α

^{1).} AB replaces BB when T2, T1, T0 = 0, 1, 1, see Table 5-7 Test modes on page 40

Table 5-5 Description of	Symbols
Symbol	Description
A	Acknowledge
MA0, MA1	Address selection bits, see Table 5-6 Address selection on page 40
N14 to N0	programmable divider bits: $N = 2^{14} \times N14 + 2^{13} \times N13 + + 2^{3} \times N3 + 2^{2} \times N2 + 2^{1} \times N1 + N0$
СР	charge pump current bit: bit = 0: charge pump current = 60 μA bit = 1: charge pump current = 280μA (default)
T0, T1, T2	test bits, see Table 5-7 Test modes on page 40
RSA, RSB	reference divider bits, see Table 5-8 Reference divider ratios on page 40
OS	tuning amplifier control bit: bit = 0: enable V_T bit = 1: disable V_T (default)
P0, P1, P2, P3	PNP ports control bits bit = 0: Port is inactive, high impedance state (default) bit = 1: Port is active, V _{OUT} = V _{CC} -V _{CESAT}
P4, P5, P6, P7	NPN ports control bits bit = 0: Port is inactive, high impedance state (default) bit = 1: Port is active, V _{OUT} = V _{CESAT}
ATC	AGC time constant bit bit = 0: I_{AGC} =220nA; Δt =2s with C=160nF (default) bit = 1: I_{AGC} =9 μ A; Δt =50ms with C=160nF

Table 5-5 Description of Symbols					
AL0, AL1, AL2	AGC take-over point bits				
POR	Power-on reset flag; POR =1 at power-on				
FL	PLL lock flag bit = 1: loop is locked				
AGC	internal AGC flag. AGC=1 when internal AGC is active (level below 3V)				
A0, A1, A2	digital output of the 5-level ADC				

Table 5-6 Address selection							
Voltage at AS	MA1	MA0					
(0 to 0.1) * V _{CC}	0	0					
open circuit	0	1					
(0.4 to 0.6) * V _{CC}	1	0					
(0.9 to 1) * V _{CC}	1	1					

Table 5-7 Test modes			
Mode	T2	T1	ТО
Normal operation	0	0	0
Normal operation (default)	0	0	1
CP is in high-impedance state	0	1	0
byte AB will follow (otherwise byte BB will follow)	0	1	1
P4 = f _{div} output, P5 = f _{ref} output	1	0	0
not in use	1	0	1
not in use	1	1	0
not in use	1	1	1

Table 5-8 Reference divider ratios								
Reference divider ratio	f _{ref} 1).	RSA	RSB					
80	50 kHz	0	0					
128	31.25 kHz	0	1					
24	166.7 kHz	1	0					
64	62.5 kHz	1	1					

^{1).} With a 4 MHz quartz

Table 5-9 AGC take-over point								
IF output level, symmetrical mode	Remark	AL2	AL1	AL0				
115 dBµV		0	0	0				
115 dBμV		0	0	1				
112 dBμV	default mode at POR	0	1	0				
109 dBμV		0	1	1				
106 dBμV		1	0	0				



Table 5-9 AGC take-over point							
103 dBµV		1	0	1			
I _{AGC} = 0	External AGC ^{1).}	1	1	0			
3.5 V	Disabled ^{2).}	1	1	1			

^{1).} The AGC detector is disabled. Both the sinking and sourcing current from the IC is disabled. The AGC output goes into a high impedance state and an external AGC source can be connected in parallel and will not be influenced.

^{2).} The AGC detector is disabled and I_{AGC} = 9 μA .

Table 5-10 A to D converter levels 1).								
Voltage at ADC	A2	A 1	A0					
(0 to 0.15) * V _{CC}	0	0	0					
(0.15 to 0.3) * V _{CC}	0	0	1					
(0.3 to 0.45) * V _{CC}	0	1	0					
(0.45 to 0.6) * V _{CC}	0	1	1					
(0.6 to 1) * V _{CC}	1	0	0					

^{1).} No erratic codes in the transition

Table 5-11 Defaults at power-on reset									
Name	Byte				В	its			
		MSB	bit6	bit5	bit4	bit3	bit2	bit1	LSB
Write Data									
Address Byte	ADB	1	1	0	0	0	MA1	MA0	R/W=0
Divider byte 1	DB1	0	Х	Х	Х	Х	Х	Х	Х
Divider byte 2	DB2	Х	Х	Х	Х	Х	Х	Х	X
Control byte	СВ	1	1	0	0	1	Х	Х	1
Bandswitch byte	BB	0	0	0	0	0	0	0	0
Auxiliary byte	AB	0	0	1	0				

Table 5-12 Internal band selection								
Band	Mixer	Oscillator						
LOW	P0. P1 1).	P0. P1						
MID	P1. P 0	P1. P 0						
HIGH ^{2).}	P0.P1	P0.P1						

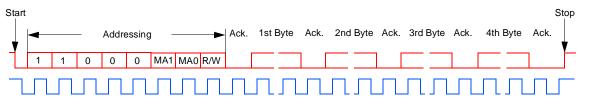
^{1).} Means: (P0 AND NOT P1); that is: LOW mixer is switched on if (P0=1 and P1=0)

^{2).} The HIGH band is selected by default

TUA6030, TUA6032



5.3 I²C Bus Timing Diagram



Telegram examples:

Start-ADB-DB1-DB2-CB-BB-Stop
Start-ADB-DB1-DB2-CB-AB-Stop
Start-ADB-CB-BB-DB1-DB2-Stop
Start-ADB-CB-AB-DB1-DB2-Stop
Start-ADB-DB1-DB2-Stop
Start-ADB-DB1-DB2-Stop
Start-ADB-CB-BB-Stop
Start-ADB-CB-BB-Stop
Start-ADB-CB-AB-Stop
Start-ADB-CB-AB-Stop

Start-ADB-CB-AB-CB-BB-Stop

Abbreviations:

Start= start condition

ADB= address byte

DB1= prog. divider byte 1

DB2= prog. divider byte 2

CB= Control byte

BB= Bandswitch byte

AB= Auxiliary byte

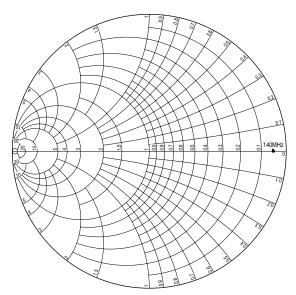
Stop= stop condition



5.4 Electrical Diagrams

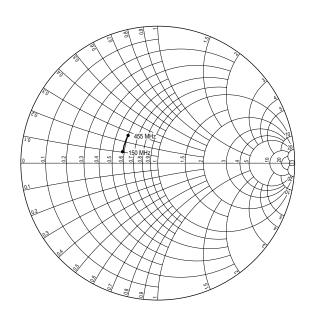
5.4.1 Input admittance (S11) of the LOW band mixer (40 to 140 MHz)





5.4.2 Input impedance (S11) of the MID band mixer (150 to 455 MHz)

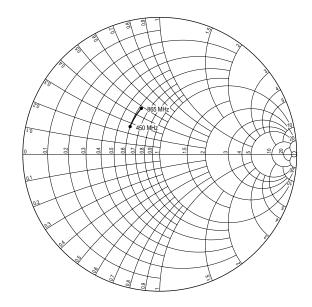
$$Z_0 = 50 \Omega$$





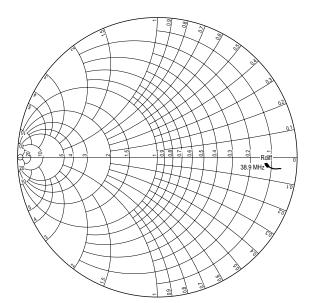
5.4.3 Input impedance (S11) of the HIGH band mixer (450 to 865 MHz)

 $Z_0 = 50~\Omega$



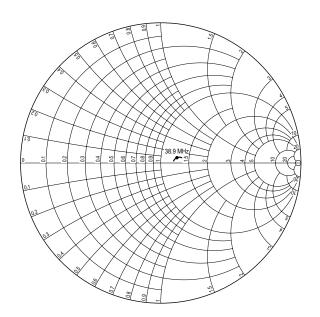
5.4.4 Output admittance (S22) of the of the Mixer output (30 to 50 MHz)

 $Y_0 = 20mS$



5.4.5 Output impedance (S22) of the IF amplifier (30 to 50 MHz)

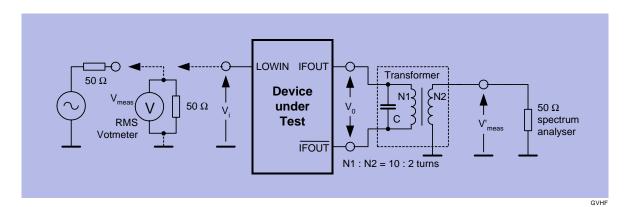
$$Z_0 = 50 \Omega$$





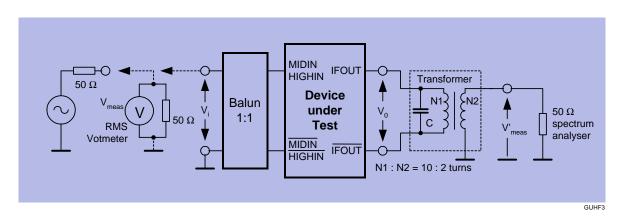
5.5 Measurement Circuits

5.5.1 Gain (G_V) measurement in LOW band



- $Z_i >> 50 Ω => V_i = 2 x V_{meas} = 80 dBμV$
- V_i = V_{meas} + 6dB = 80 dBµV
- V₀ = V'_{meas} + 16 dB (transformer ratio N1:N2 and transformer loss
- $G_v = 20 \log(V_0 / V_i)$

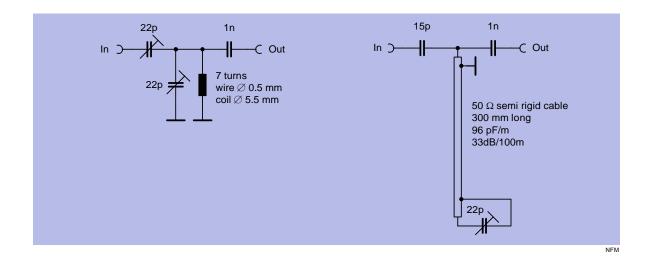
5.5.2 Gain (G_V) measurement in MID and HIGH bands



- V_i = V_{meas} = 70 dBµV
- V₀ = V'_{meas} + 16 dB (transformer ratio N1:N2 and transformer loss
- = $G_v = 20 \log(V_0 / V_i) + 1 dB (1 dB = insertion loss of balun)$



5.5.3 Matching circuit for optimum noise figure in LOW band



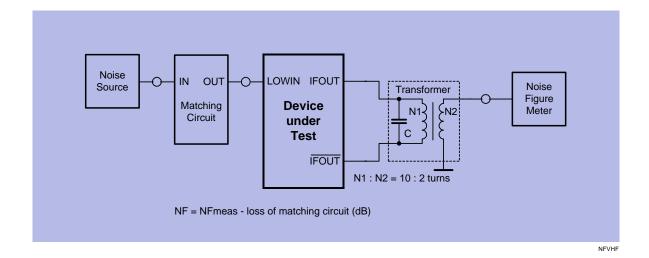
For $f_{RF} = 50 \text{ MHz}$

- loss = 0 dB
- image suppression = 16 dB

For $f_{RF} = 150 \text{ MHz}$

- loss = 1.3 dB
- image suppression = 13 dB

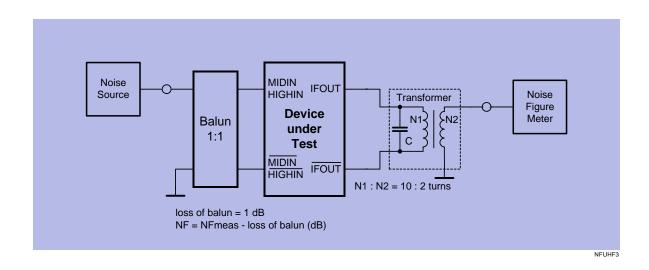
5.5.4 Noise figure (NF) measurement in LOW band



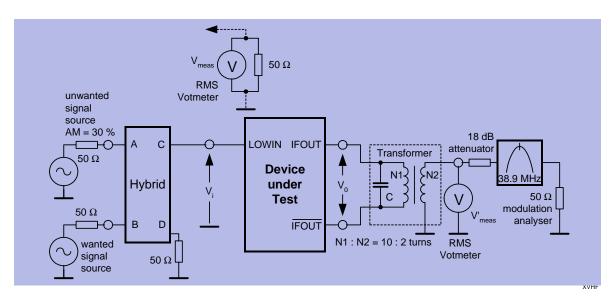
Wireless Components 5 - 47 Specification, July 2001



5.5.5 Noise figure (NF) measurement in MID and HIGH bands



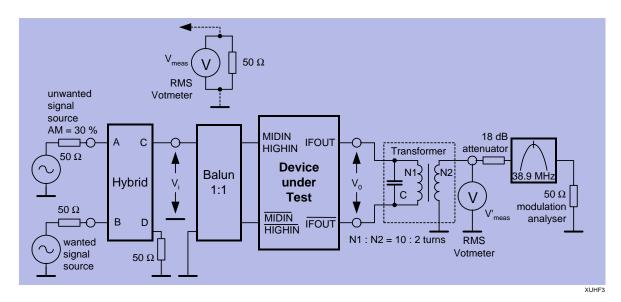
5.5.6 Cross modulation measurement in LOW band



- $Z_i >> 50 \Omega => V_i = 2 \times V_{meas}$
- V'_{meas} = V₀ 16 dB (transformer ratio N1:N2 and transformer loss)
- wanted output signal at f_{pix}, V_o = 100 dBμV
- unwanted output signal at f_{snd}

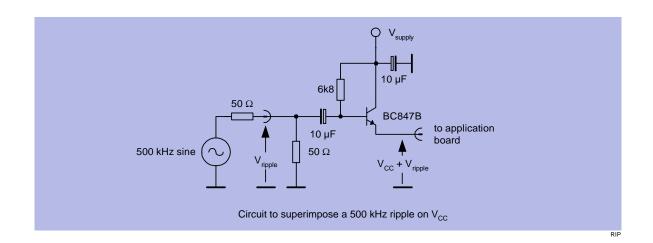


5.5.7 Cross modulation measurement in MID and HIGH bands



- V'_{meas} = V₀ 16 dB (transformer ratio N1:N2 and transformer loss)
- wanted output signal at f_{pix}, V_o = 100 dBμV
- unwanted output signal at f_{snd}

5.5.8 Ripple susceptibility measurement



Wireless Components 5 - 49 Specification, July 2001